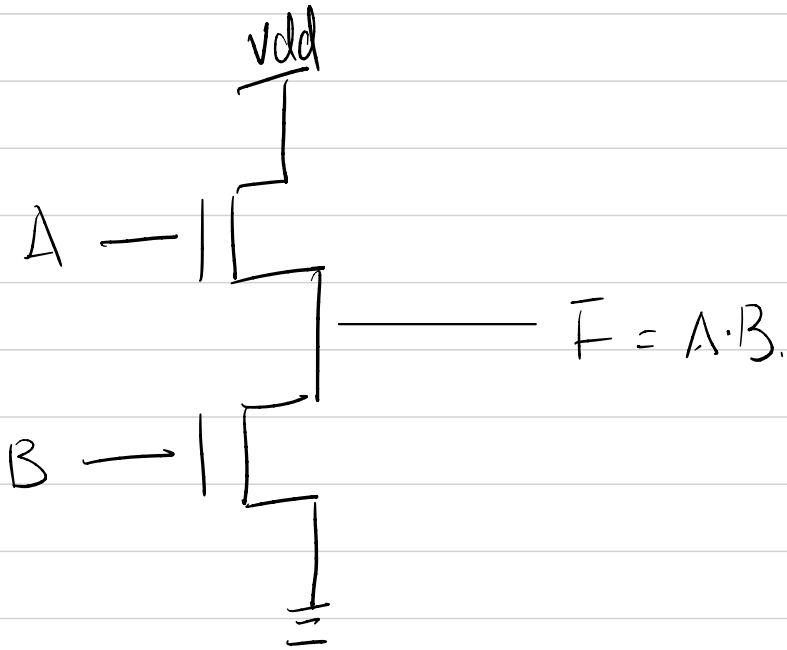


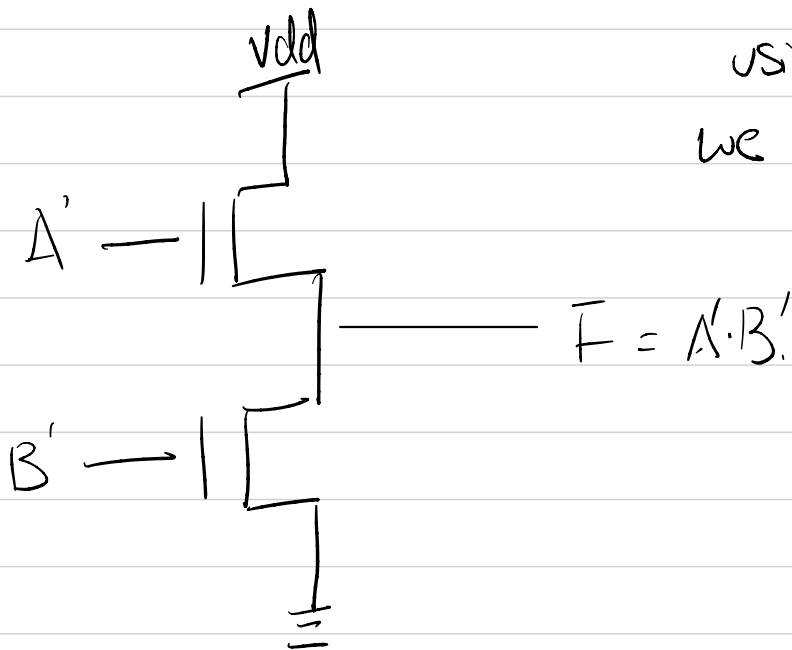
EE 477L HW2

Q1)

a)

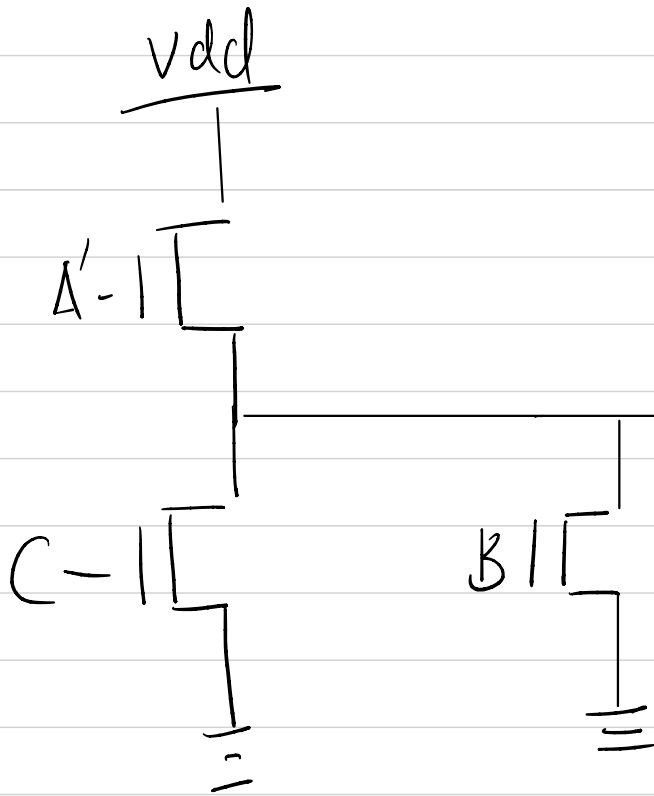


b).



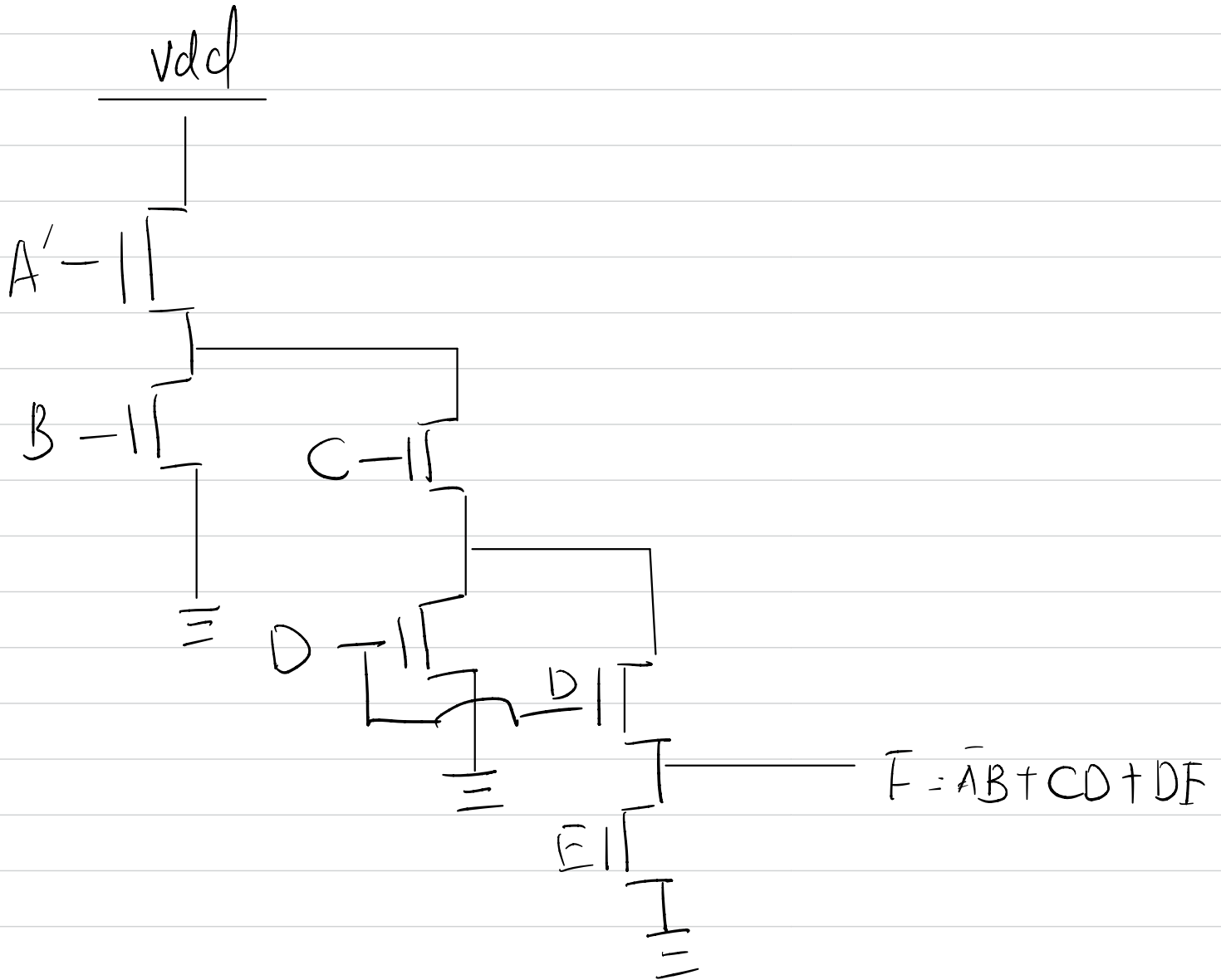
using de morgan's,
we set $(A+B)' = A' \cdot B'$

c)



$$F = \overline{A}C + B$$

d).



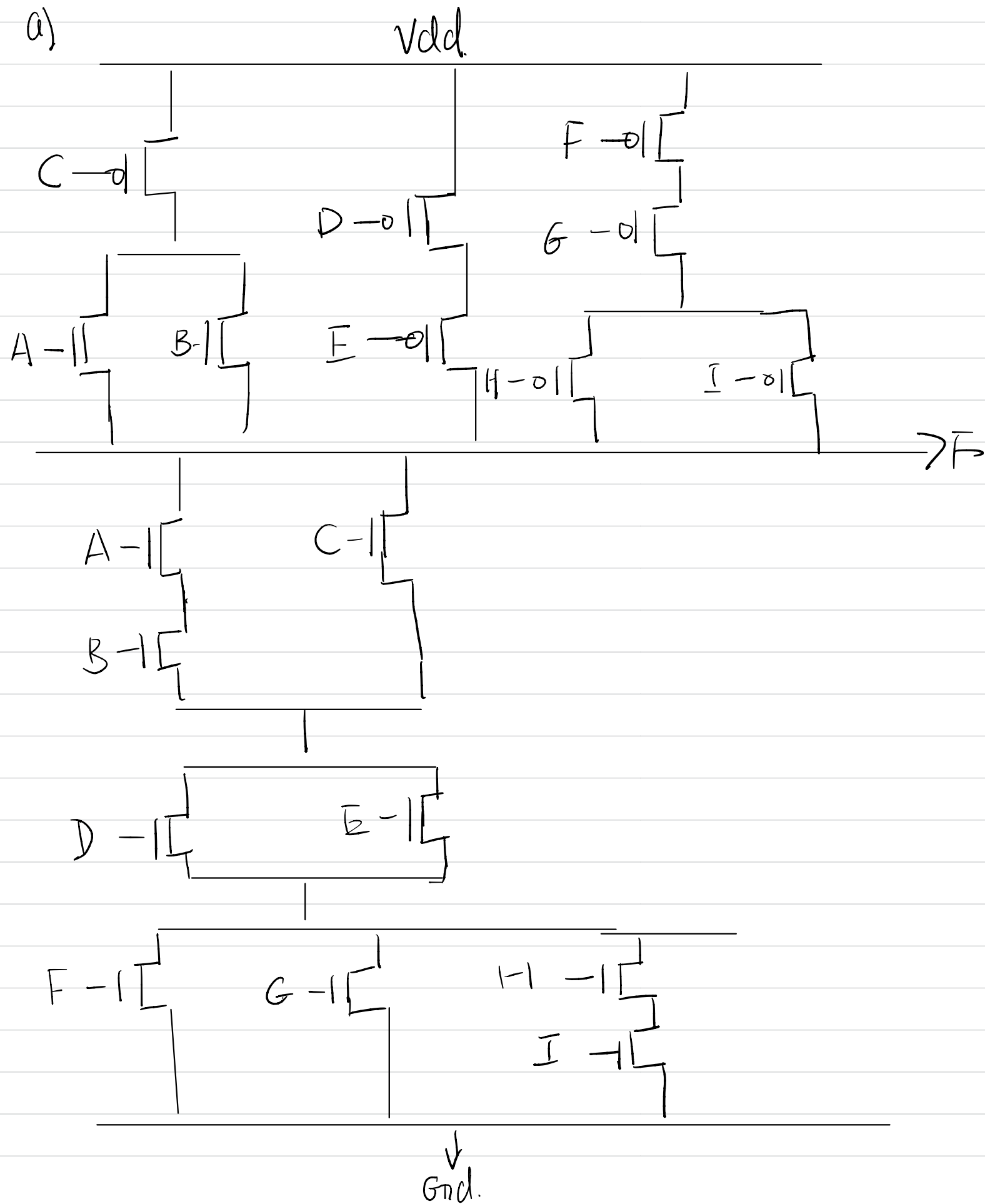
Q2).

Because NAND is more Power-efficient compare w/ NOR, and it's also easier to implement.

But NOR may be preferred because it's faster than NAND.

Q3)

a)



b) (I didn't really get this question ...)

w/ mobility ratio of 2, it means the PMOS transistors should be 2x width of the NMOS transistors,

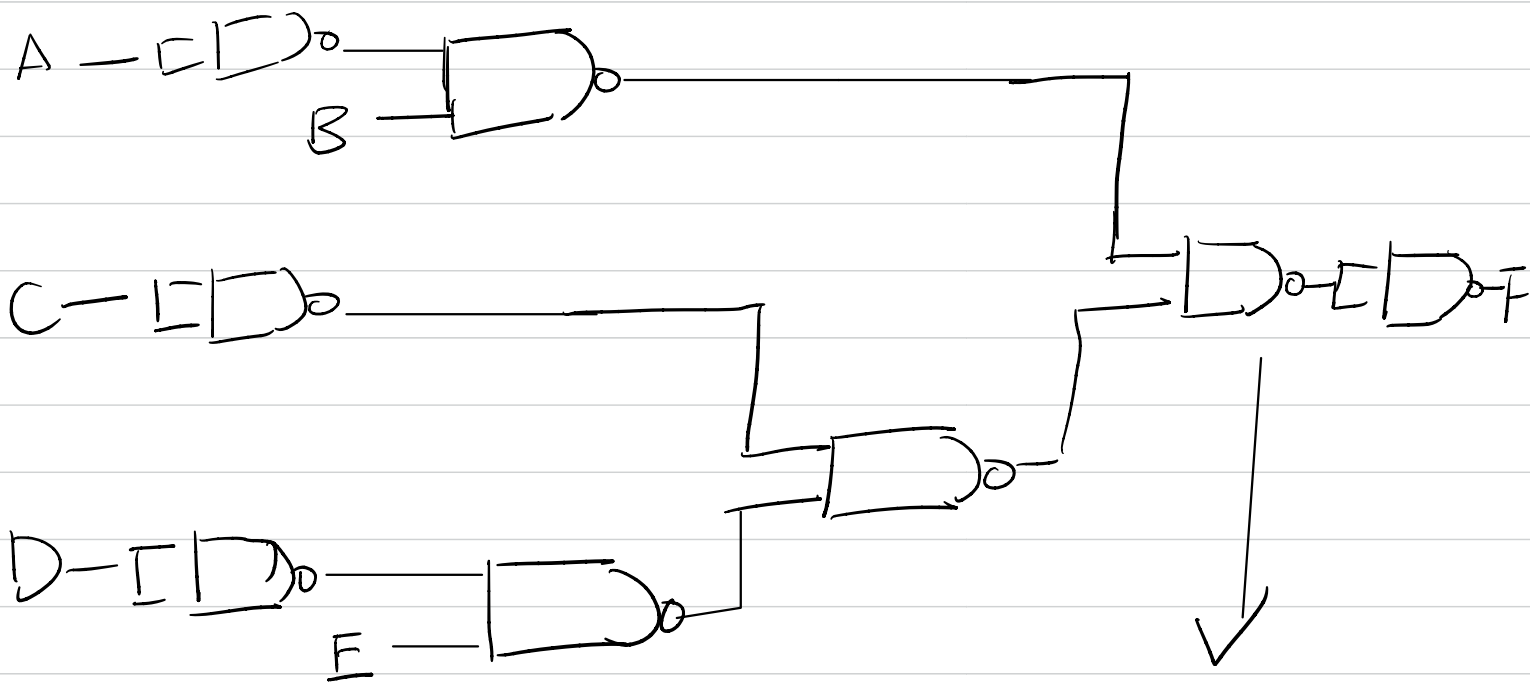
Q4)

$$(A + \bar{B}) = \overline{\bar{A} B}$$

$$(C + D \bar{E}) = \overline{\bar{C} \overline{D \bar{E}}}$$

$$\therefore F = \overline{\bar{A} B} \cdot \overline{\bar{C} \overline{D \bar{E}}}$$

Using NAND:



Using 2 NAND

to perform 5 AND

Q5).

a) The green thing is n-wall, which helps to isolate PMOS transistors, NMOS does not need it because it won't bias even without the n-wall, no-change would made if we add n-wall around n-mos. since NMOS can directly fabricate from p-type substrate.

b)

